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Cora M. Utley  
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**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of Christopher L. Chua

Group Art Unit: 2828

Application No.: 10/625,811

Examiner: Tuan N. Nguyen

Filed: July 23, 2003

Confirmation No.: 7775

For: PHASE ARRAY OXIDE-CONFINED VCSELS

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<b>INFORMATION DISCLOSURE STATEMENT</b> (Use several sheets if necessary)				APPLICANT(S) <b>Christopher L. Chua</b>	
				FILING DATE <b>7/23/2003</b>	GROUP <b>2828</b>
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